



1. Description

SS028N10LS, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for BMS and high current switching applications.

KEY CHARACTERISTICS

Parameter	Value	Unit
V_{DS}	100	V
I_D	250	A
$R_{DS(on).typ}$	2.2	mΩ

FEATURES

- Fast Switching
- Low On-Resistance ($R_{DS(on)} \leq 2.8m\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

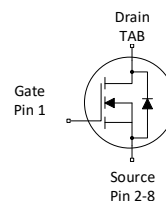
APPLICATIONS

- BMS
- High current switching applications

ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing	Quantity
SS028N10LS	TOLL-8L	SS028N10LS	Reel	2000

SchematicDiagram



TOLL-8L

